

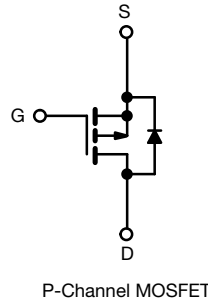
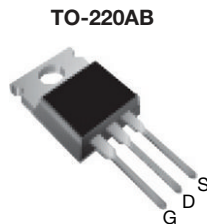


THE DATASHEET OF IRF9Z34PBF



Power MOSFET

| PRODUCT SUMMARY | |
|---------------------------|-------------------------|
| V_{DS} (V) | -60 |
| $R_{DS(on)}$ (Ω) | $V_{GS} = -10$ V 0.14 |
| Q_g max. (nC) | 34 |
| Q_{gs} (nC) | 9.9 |
| Q_{gd} (nC) | 16 |
| Configuration | Single |



FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

| ORDERING INFORMATION | |
|----------------------|-------------|
| Package | TO-220AB |
| Lead (Pb)-free | IRF9Z34PbF |
| | SiHF9Z34-E3 |
| SnPb | IRF9Z34 |
| | SiHF9Z34 |

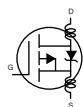

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | | |
|---|-------------------|----------------|----------------|-------|----------|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V_{DS} | -60 | V | |
| Gate-Source Voltage | | V_{GS} | ± 20 | | |
| Continuous Drain Current | V_{GS} at -10 V | I_D | $T_C = 25$ °C | -18 | A |
| | | | $T_C = 100$ °C | -13 | |
| Pulsed Drain Current ^a | | I_{DM} | -72 | | |
| Linear Derating Factor | | | 0.59 | W/°C | |
| Single Pulse Avalanche Energy ^b | | E_{AS} | 370 | mJ | |
| Repetitive Avalanche Current ^a | | I_{AR} | -18 | A | |
| Repetitive Avalanche Energy ^a | | E_{AR} | 8.8 | mJ | |
| Maximum Power Dissipation | $T_C = 25$ °C | P_D | 88 | W | |
| Peak Diode Recovery dV/dt ^c | | dV/dt | -4.5 | V/ns | |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +175 | °C | |
| Soldering Recommendations (Peak temperature) ^d | for 10 s | | 300 | | |
| Mounting Torque | 6-32 or M3 screw | | 10 | | lbf · in |
| | | | 1.1 | N · m | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, $L = 1.3$ mH, $R_g = 25$ Ω , $I_{AS} = -18$ A (see fig. 12).
- $I_{SD} \leq -18$ A, $dI/dt \leq 170$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.



| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Case-to-Sink, Flat, Greased Surface | R_{thCS} | 0.50 | - | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 1.7 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|---|---------------------|---|------|--------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | -60 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}, I_D = -1\text{ mA}$ | - | -0.060 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | -2.0 | - | -4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$ | - | - | -100 | μA |
| | | $V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$ | - | - | -500 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}, I_D = -11\text{ A}^b$ | - | - | 0.14 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = -25\text{ V}, I_D = -11\text{ A}^b$ | 5.9 | - | - | S |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 | - | 1100 | - | μF |
| Output Capacitance | C_{oss} | | - | 620 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 100 | - | |
| Total Gate Charge | Q_g | $V_{GS} = -10\text{ V}, I_D = -1.8\text{ A}, V_{DS} = -48\text{ V}$, see fig. 6 and 13 ^b | - | - | 34 | nC |
| Gate-Source Charge | Q_{gs} | | - | - | 9.9 | |
| Gate-Drain Charge | Q_{gd} | | - | - | 16 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -30\text{ V}, I_D = -18\text{ A}, R_g = 12\text{ }\Omega, R_D = 1.5\text{ }\Omega$, see fig. 10 ^b | - | 18 | - | ns |
| Rise Time | t_r | | - | 120 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 20 | - | |
| Fall Time | t_f | | - | 58 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact  | - | 4.5 | - | nH |
| Internal Source Inductance | L_S | | - | 7.5 | - | |
| Gate Input Resistance | R_g | $f = 1\text{ MHz}$, open drain | 0.7 | - | 3.9 | Ω |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p-n junction diode  | - | - | -18 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | - | - | -72 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = -18\text{ A}, V_{GS} = 0\text{ V}^b$ | - | - | -6.3 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = -18\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | - | 100 | 200 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 0.28 | 0.52 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

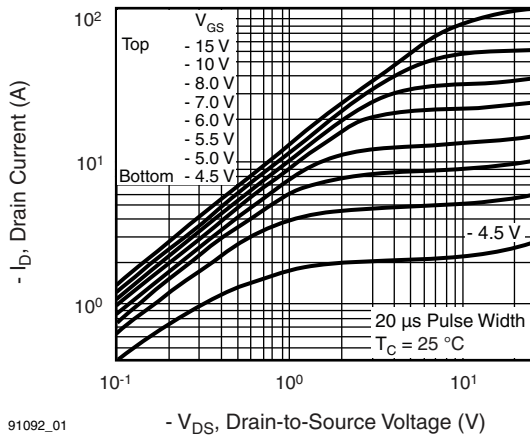


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

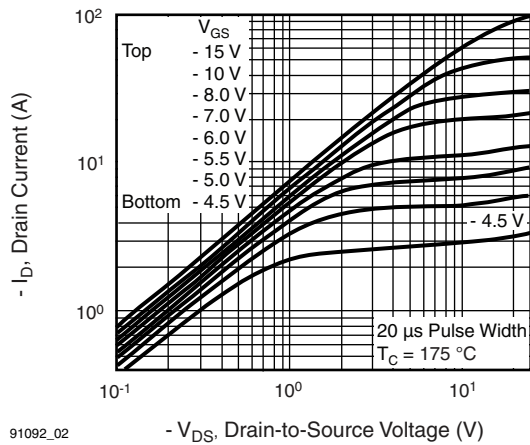


Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^\circ\text{C}$

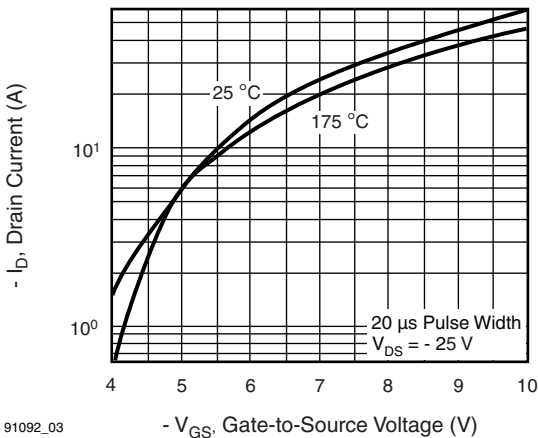


Fig. 3 - Typical Transfer Characteristics

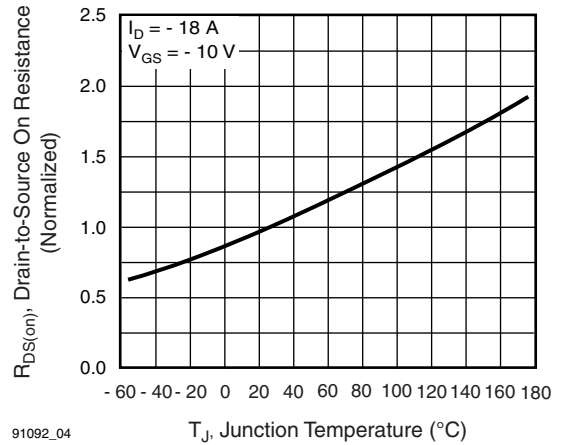


Fig. 4 - Normalized On-Resistance vs. Temperature

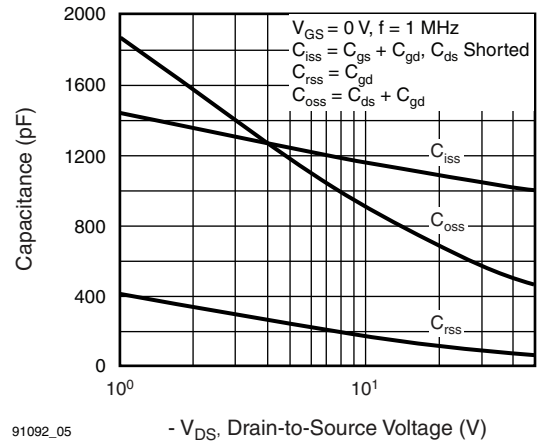


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

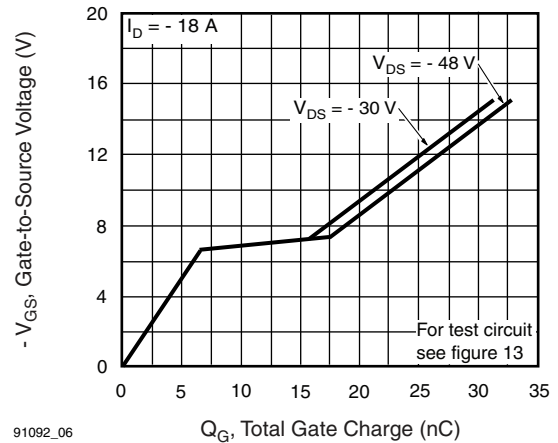
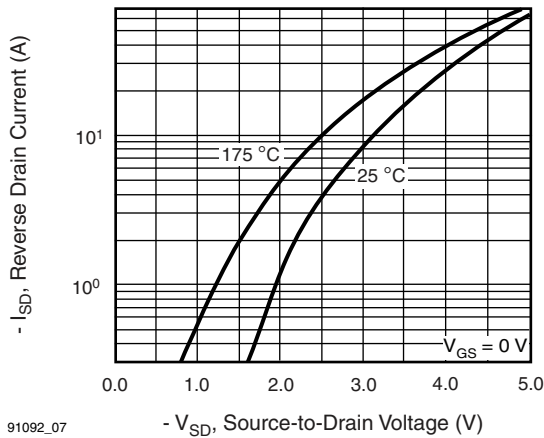
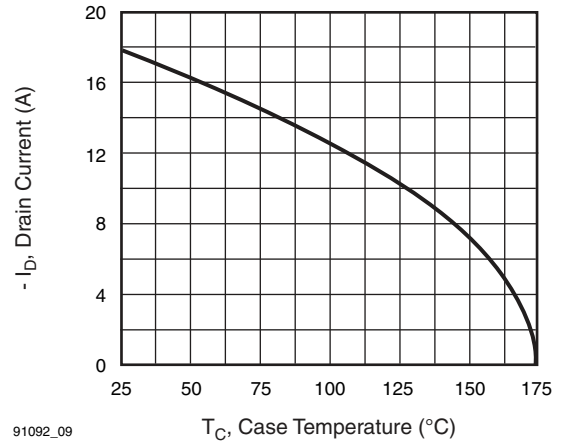


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



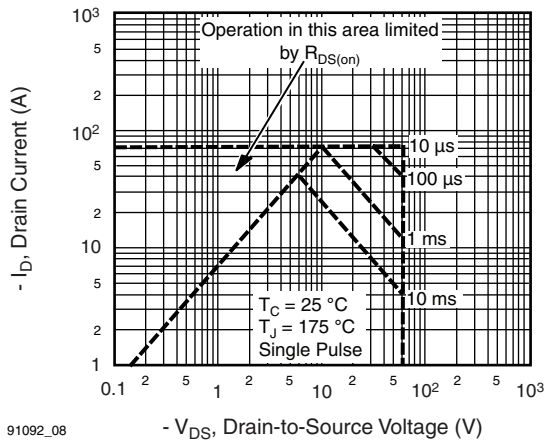
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 9 - Maximum Drain Current vs. Case Temperature



91092_08

Fig. 8 - Maximum Safe Operating Area

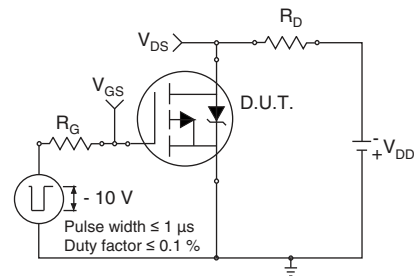


Fig. 10a - Switching Time Test Circuit

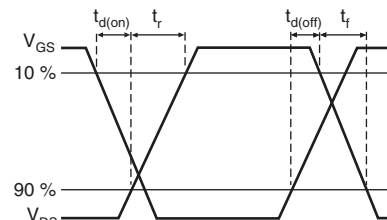
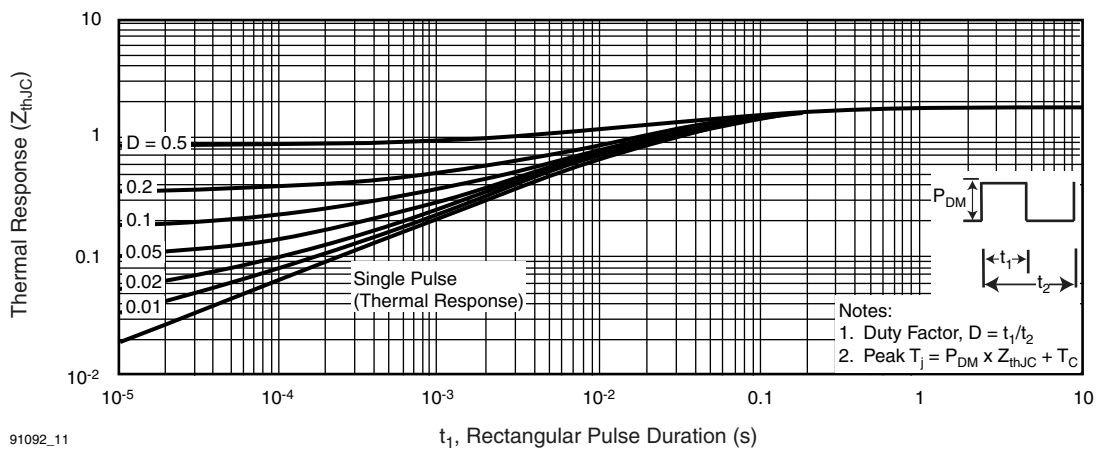


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

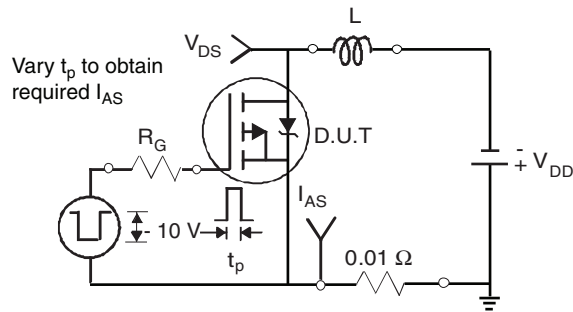


Fig. 12a - Unclamped Inductive Test Circuit

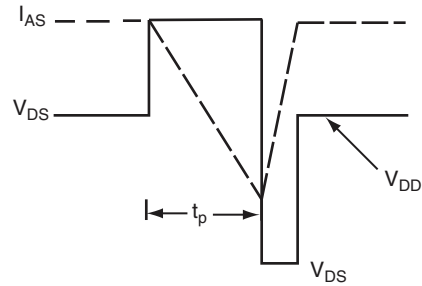


Fig. 12b - Unclamped Inductive Waveforms

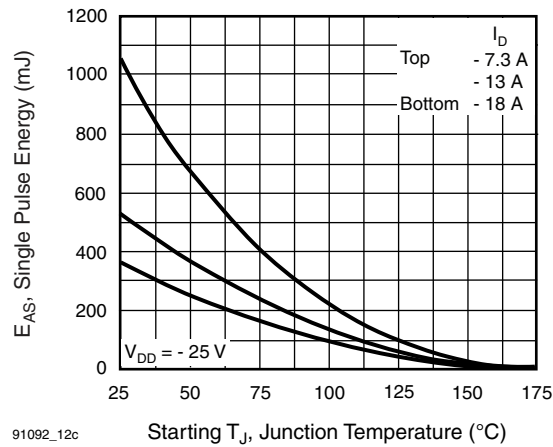


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

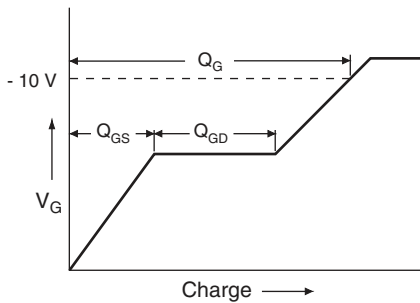


Fig. 13a - Basic Gate Charge Waveform

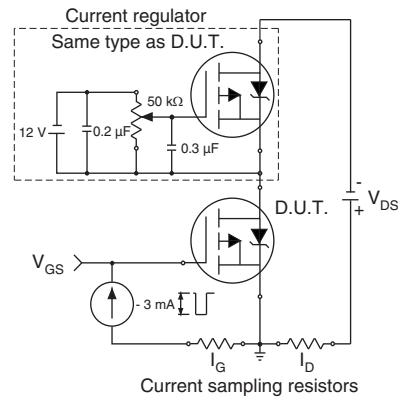
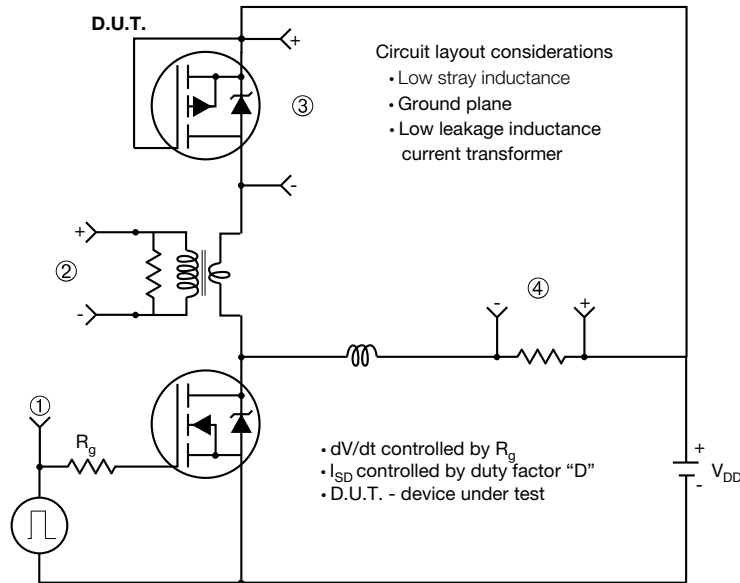
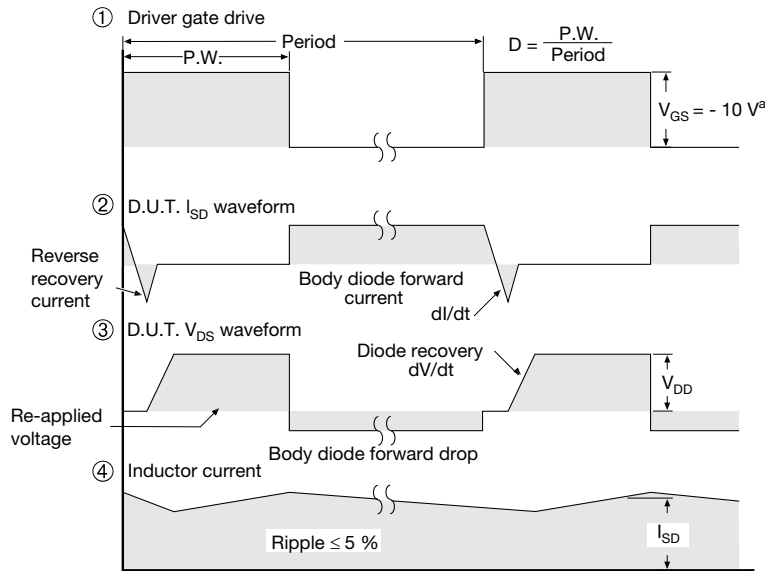


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
 • Compliment N-Channel of D.U.T. for driver



Note
 a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91092>.

TO-220-1



| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.24 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.02 | 0.027 | 0.040 |
| b(1) | 1.14 | 1.78 | 0.045 | 0.070 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.33 | 15.85 | 0.564 | 0.624 |
| E | 9.96 | 10.52 | 0.392 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.10 | 6.71 | 0.240 | 0.264 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.36 | 14.40 | 0.526 | 0.567 |
| L(1) | 3.33 | 4.04 | 0.131 | 0.159 |
| Ø P | 3.53 | 3.94 | 0.139 | 0.155 |
| Q | 2.54 | 3.00 | 0.100 | 0.118 |

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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